

# LArTPC Signal Processing

Bruce Baller - Fermilab

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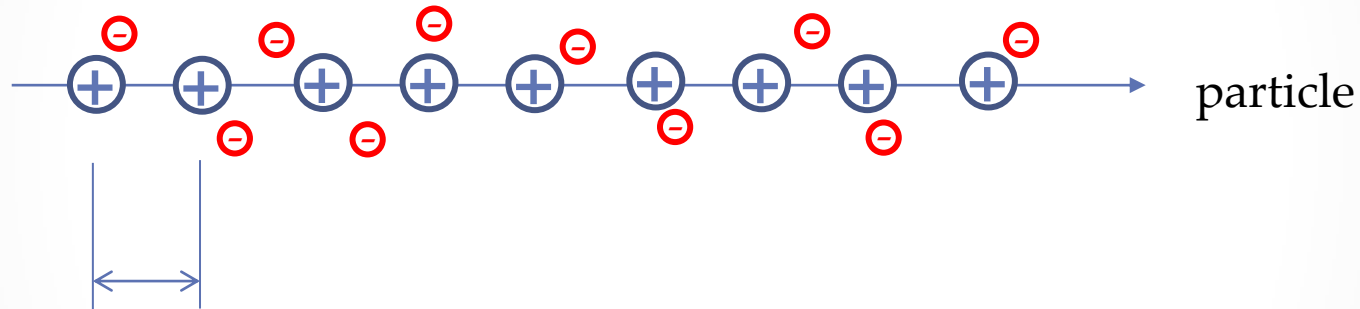
LArTPC R&D Workshop 2014

# Outline

- Liquid state signal generation
  - Ionization
  - Thermalization
  - Recombination
  - Electron attachment & diffusion
- Signal generation in wire planes
  - Field response
  - Electronics response
- Convolution and deconvolution
- Closing comments

# Ionization Nano-Physics in LAr

$r_{\text{ion-electron}} \sim 0.5 \text{ nm}$  with  $E_{\text{electron}} \sim 5 \text{ eV}$



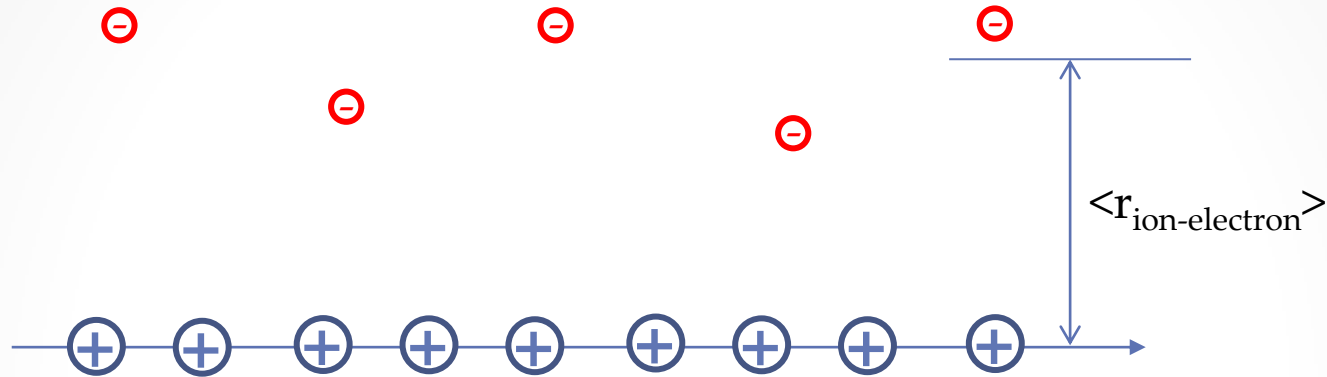
$$r_{\text{ion}} = 23.6 \text{ eV} / (dE/dx)$$

MIP  $dE/dx = 2.1 \text{ MeV/cm} \rightarrow r_{\text{ion}} \sim 100 \text{ nm}$

HIP  $dE/dx \sim 25 \text{ MeV/cm} \rightarrow r_{\text{ion}} \sim 10 \text{ nm}$

Ref: LAr atomic spacing  $\sim 0.4 \text{ nm}$  ( $= 4 \text{ \AA}$ )

# After Thermalization



Electron mfp = 20 nm  
Onsager distance 120 nm  
( $E_{\text{Coulomb}} = E_{\text{thermal}}$ )



~10k collisions  
~2 ns  
 $E_{\text{thermal}} \sim 0.01 \text{ eV}$   
 $\langle r_{\text{ion-electron}} \rangle \sim 2500 \text{ nm} (2.5 \mu\text{m})$

*Jaskolski, Wojcik J. Phys. Chem. A 115 (2011) 4317*  
*Sowada, Phys. Rev. B 25 (1982) 3434*

# Recombination Theories

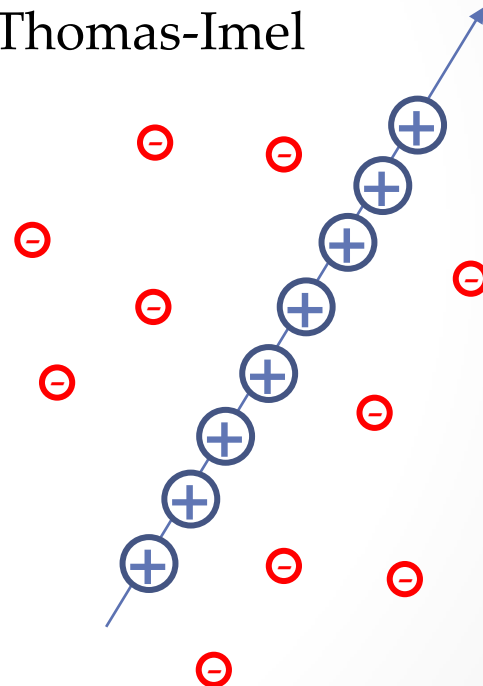
## Geminate

Small  $r_{\text{ion-electron}}$   
~0.1% in LAr  
Onsager



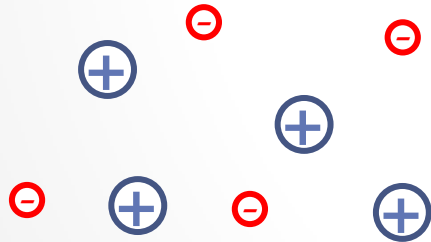
## Columnar

Large  $r_{\text{ion-electron}}$   
Jaffe, Thomas-Imel



## Bulk

Debye-Smoluchowski



## 2. Zur Theorie der Ionisation in Kolonnen; von George Jaffé.

Leipzig, im Mai 1913.

(Eingegangen 30. Mai 1913.)

$$(32') \quad Y_3(X) = \frac{1}{1 + \frac{\alpha N_0}{8 \pi D} \sqrt{\frac{\pi}{z'}} S(z')}, \quad z' = \frac{b^2 u^2 X^2 \sin^2 \varphi}{2 D^2}.$$

→ Birks model (1951)

$Y_3(X)$  = recombination factor  $\mathcal{R}$   
→ fraction of electrons that escape vs E field strength  $X$

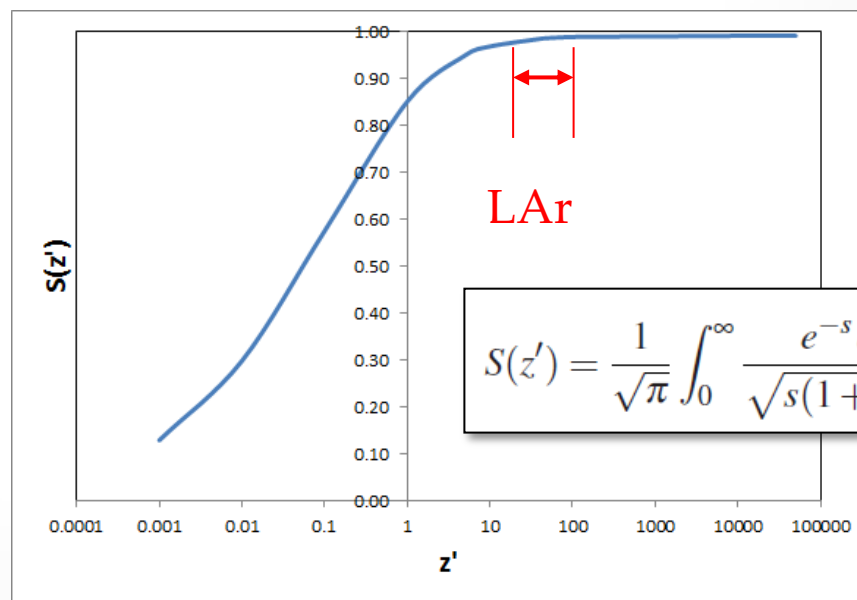
### Assumptions

Recombination ~ charge density

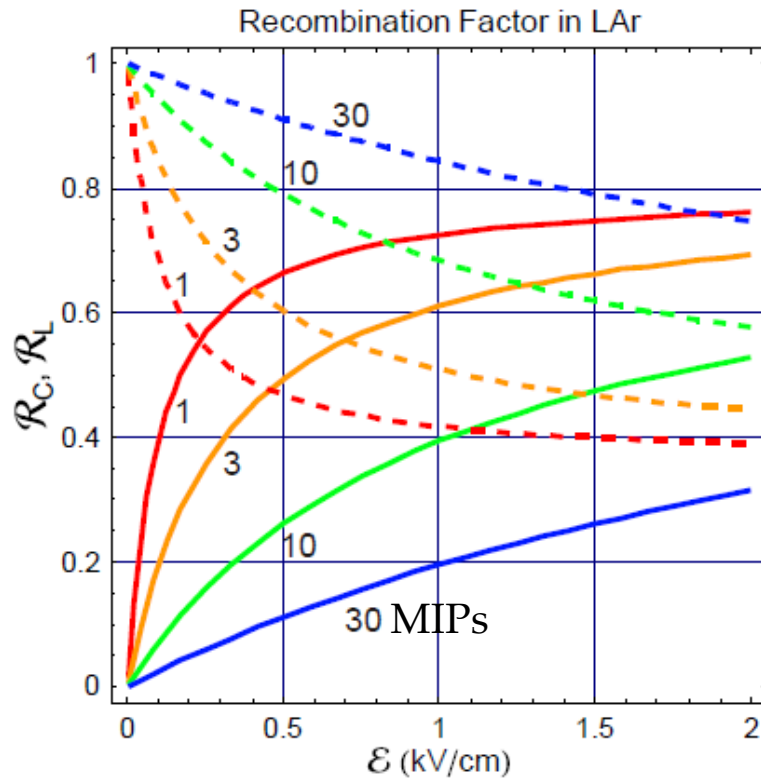
No Coulomb interactions

Ion mobility = electron mobility

Electrons & ions have the same  
Gaussian distribution



# Recombination in Practice



$$R_C = \frac{Q}{Q_\infty} = \frac{A}{1 + \frac{k}{\mathcal{E}} \times \frac{dE}{dx}}$$

Charge recombination factor

$$R_L = \frac{L}{L_0} = 1 - \alpha R_C$$

Light recombination factor

$\mathcal{E}$  is electric field in kV / cm

ICARUS

$$A = 0.800 + 0.003$$

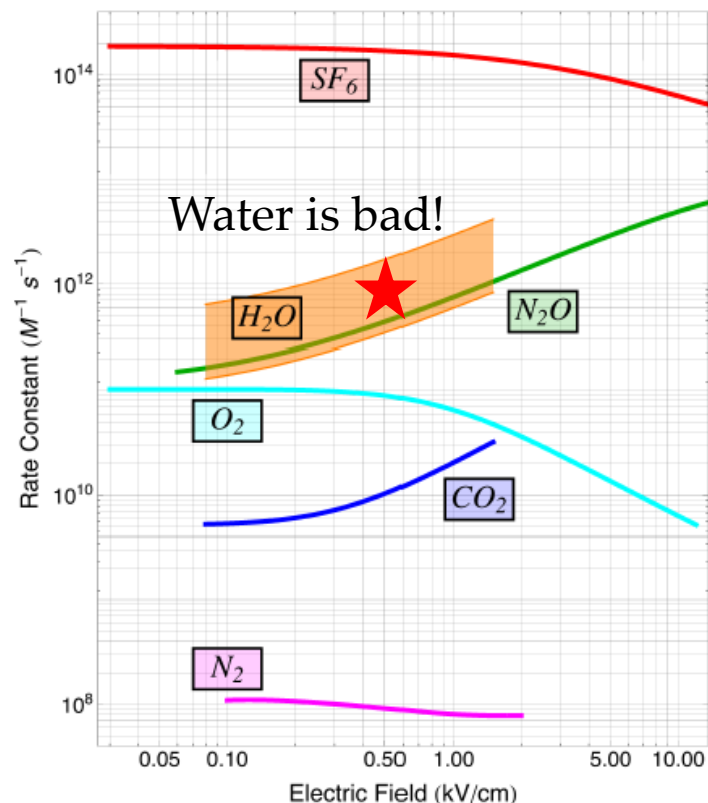
$$k = 0.0486 + 0.0006 \text{ kV/cm (g/cm}^2\text{/MeV)}$$

Amoruso, et al NIM A 523 (2004) 275

Less charge = more scintillation light

# Electron Attachment & Diffusion

Electron Attachment Rate Constants in LAr



$Q_0$  = electron charge after recombination  
 $Q$  = charge arriving at the wire planes

“drift electron lifetime”

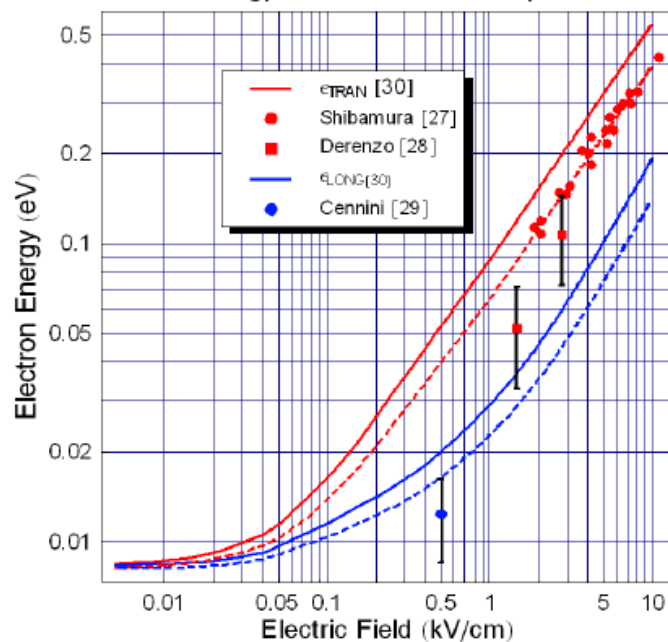
$$\tau_{\text{electron}} = 1 / (\text{Rate Constant} \times \text{concentration})$$

$$Q = Q_0 \exp(-t_{\text{drift}} / \tau_{\text{electron}})$$

Longitudinal /  
Transverse  
diffusion rms

$$\sigma_{T(L)} = \sqrt{\frac{2 \varepsilon_{T(L)} \Delta z}{E}}$$

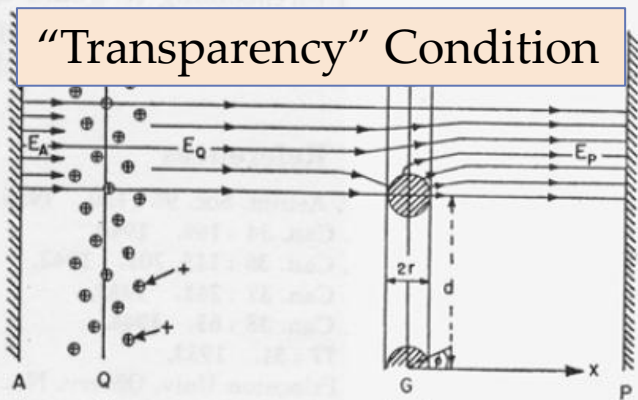
Electron Energy in LAr: Data + Theory of Artazhev





# Electron Transport in Wire Planes

“Transparency” Condition



Garfield simulation

MicroBooNE

3 mm wire spacing

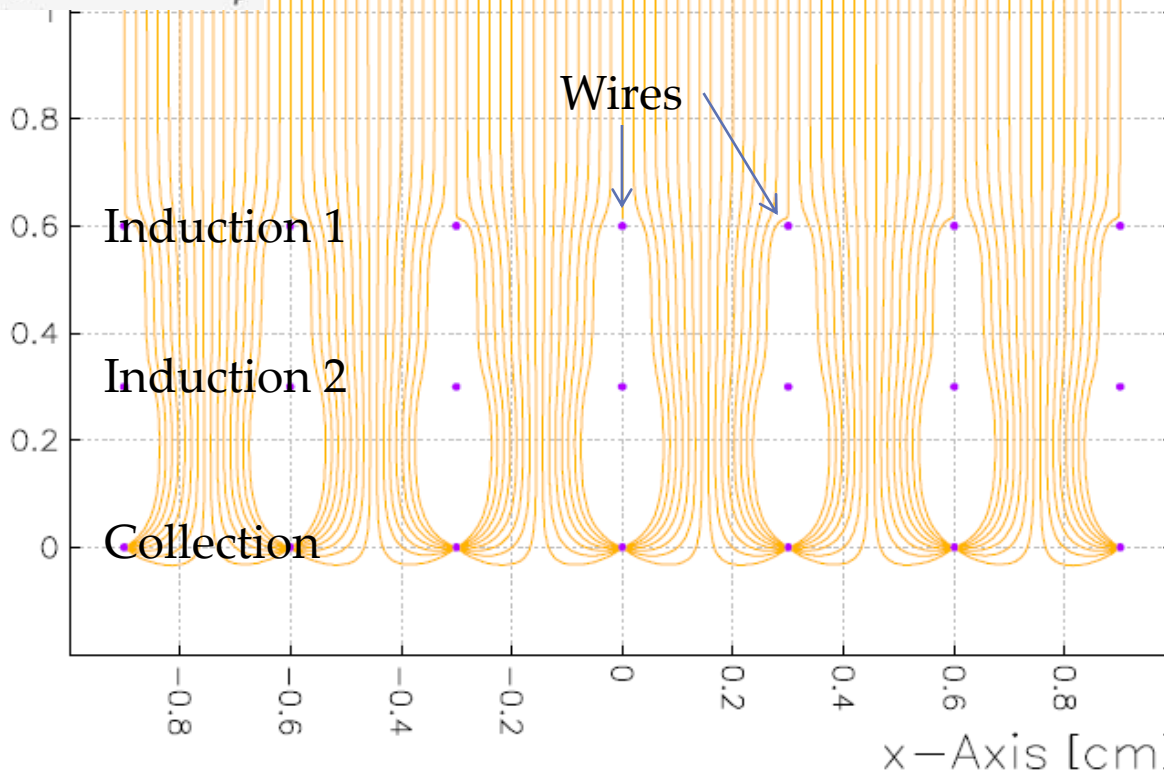
3 mm plane cap

$$\rho = 2\pi r / d$$

$$\frac{E_P}{E_Q} = \frac{1+\rho}{1-\rho}$$

1.37 for uB

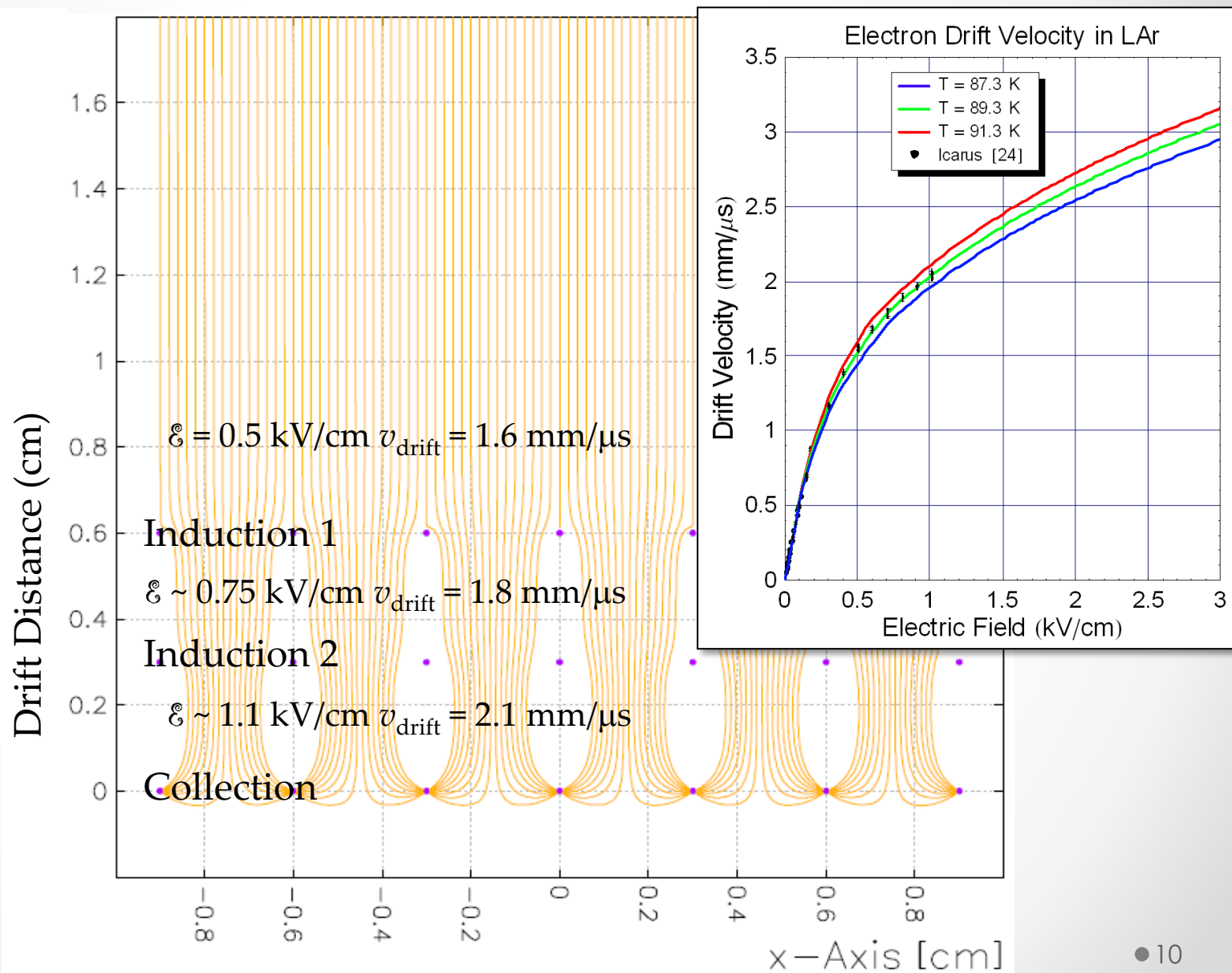
Drift Distance (cm)



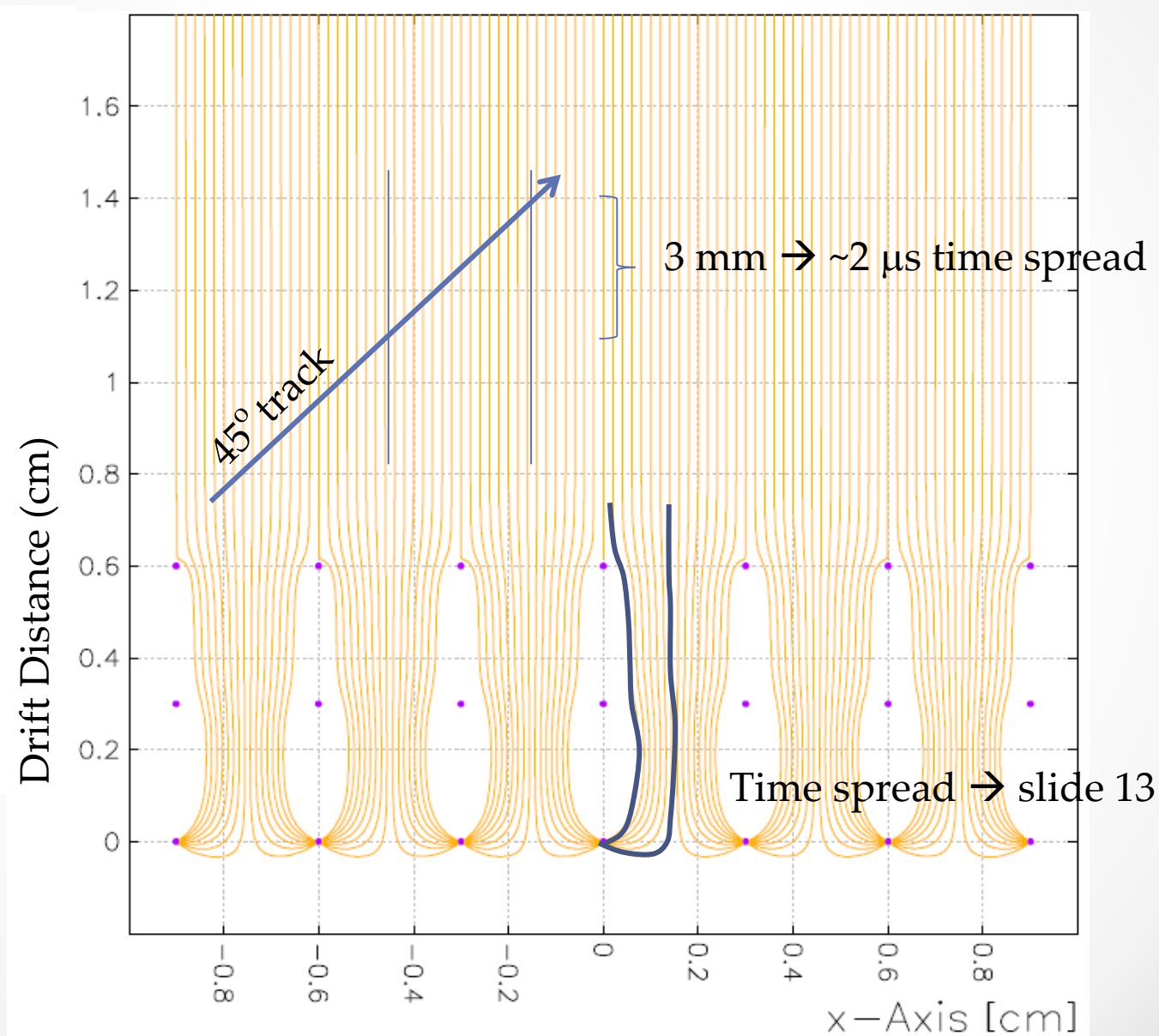
*Buneman, Can. J. Res.  
A27 (1945) 191*

# Electron Transport in Wire Planes

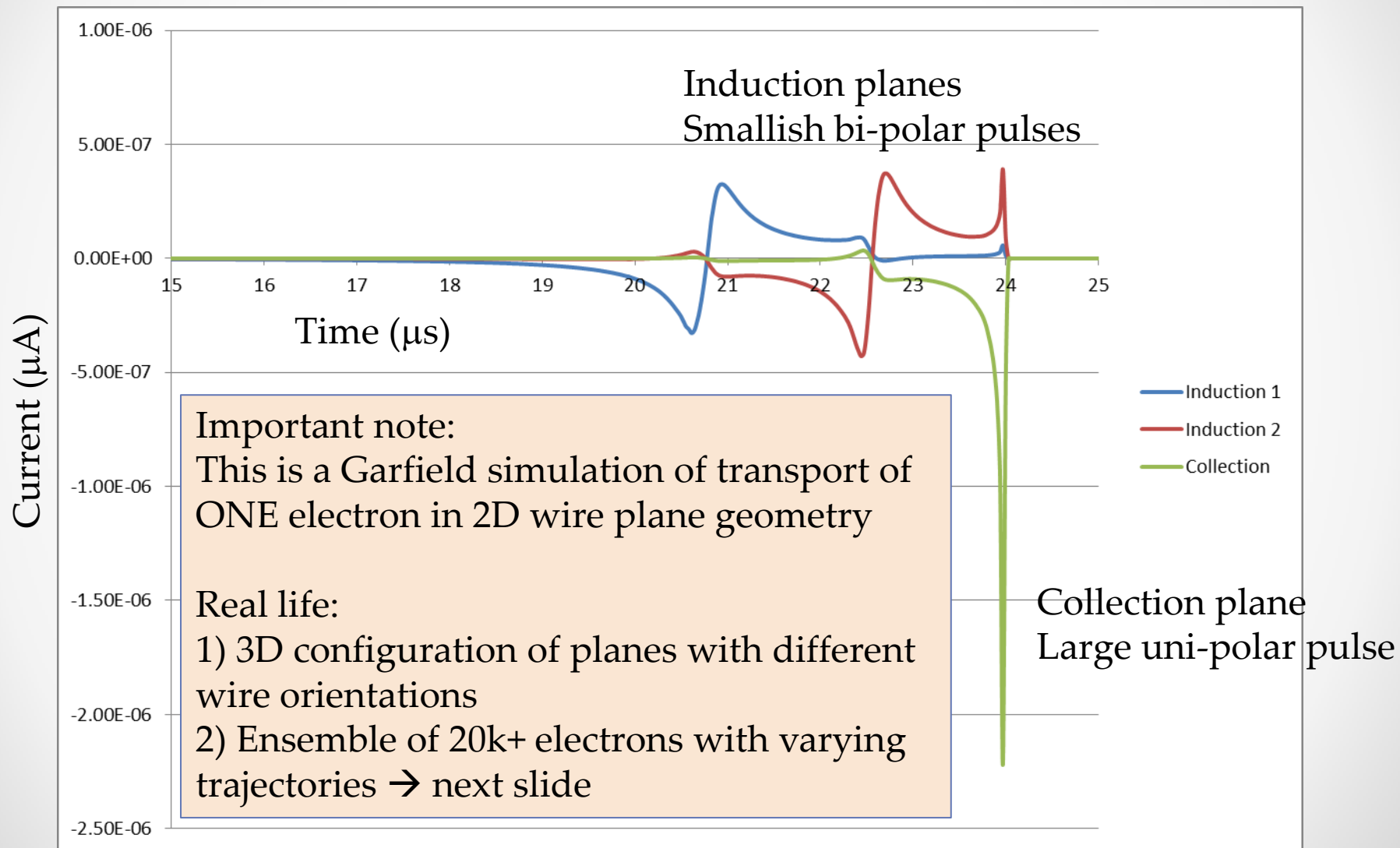
Set E field  
ratio ~ 1.5

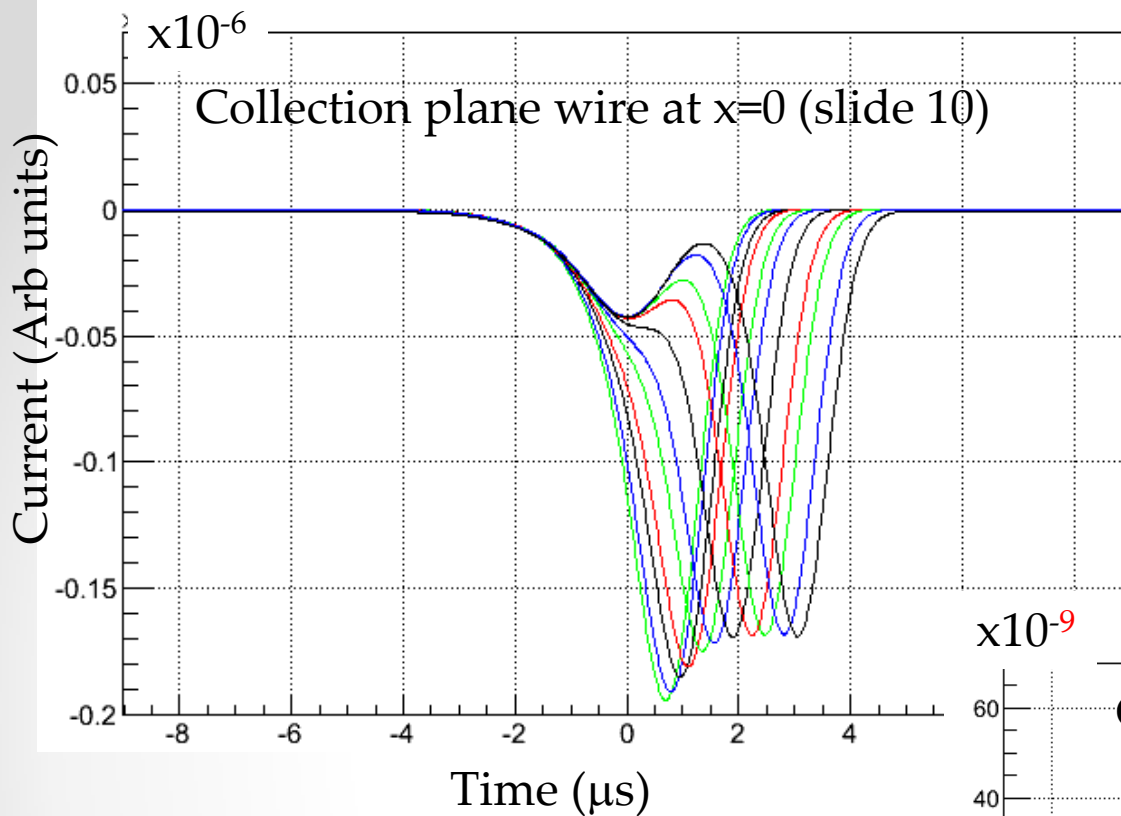


# Electron Transport in Wire Planes



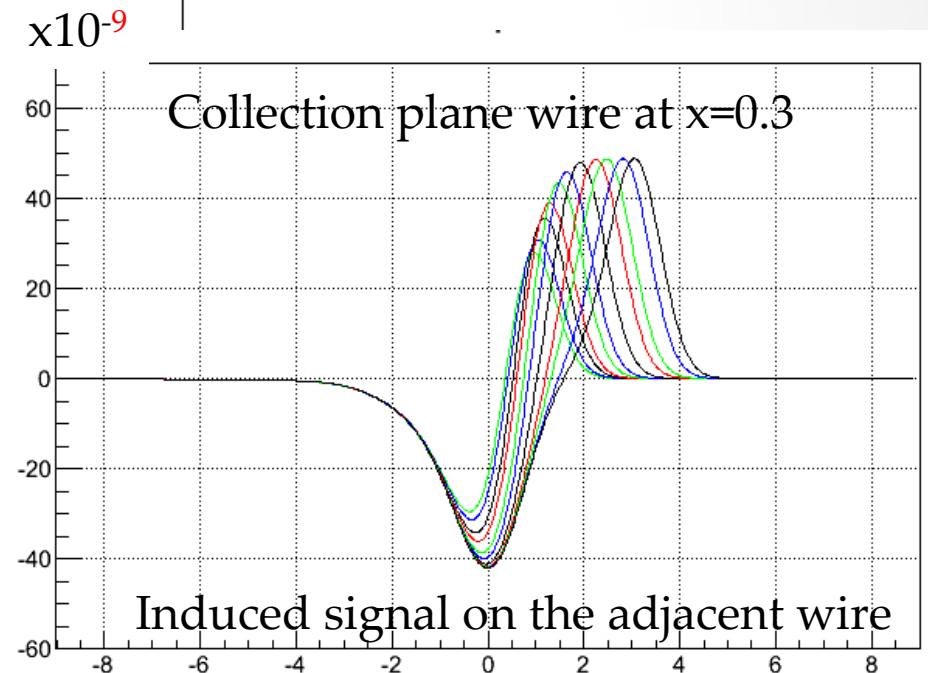
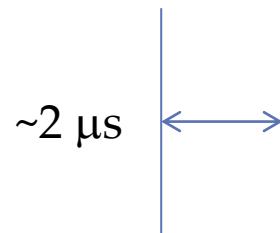
# Field Response





Convolute field response  
with  $0.5 \mu\text{s}$  electronics  
shaping time

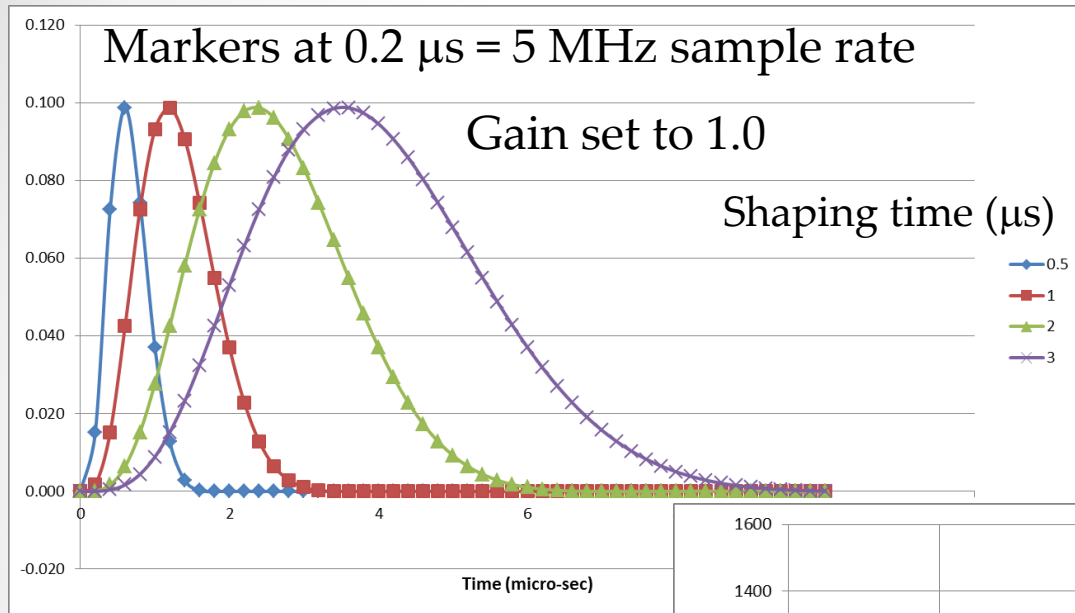
Different curves are for  
electrons starting at  
 $0 < x < 1.5 \text{ mm}$



Leon Rochester (SLAC) for MicroBooNE

# Electronics Response

*Using BNL – Nevis electronics chain*

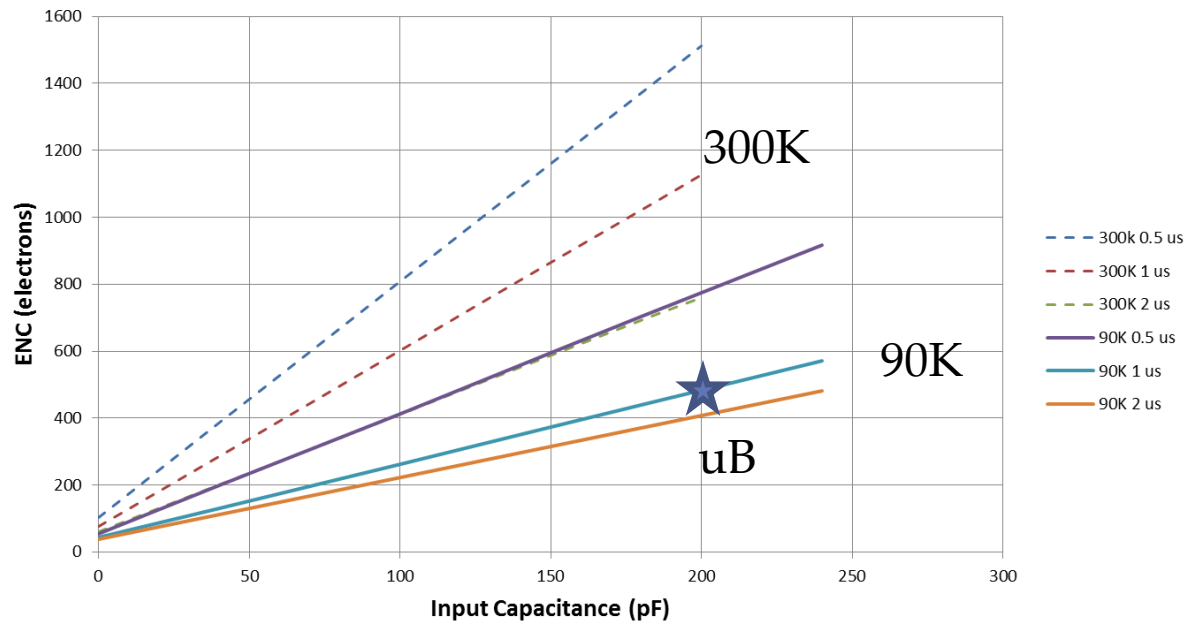


$$\text{ENC} = A + B C_{\text{in}}$$

Rough approximation

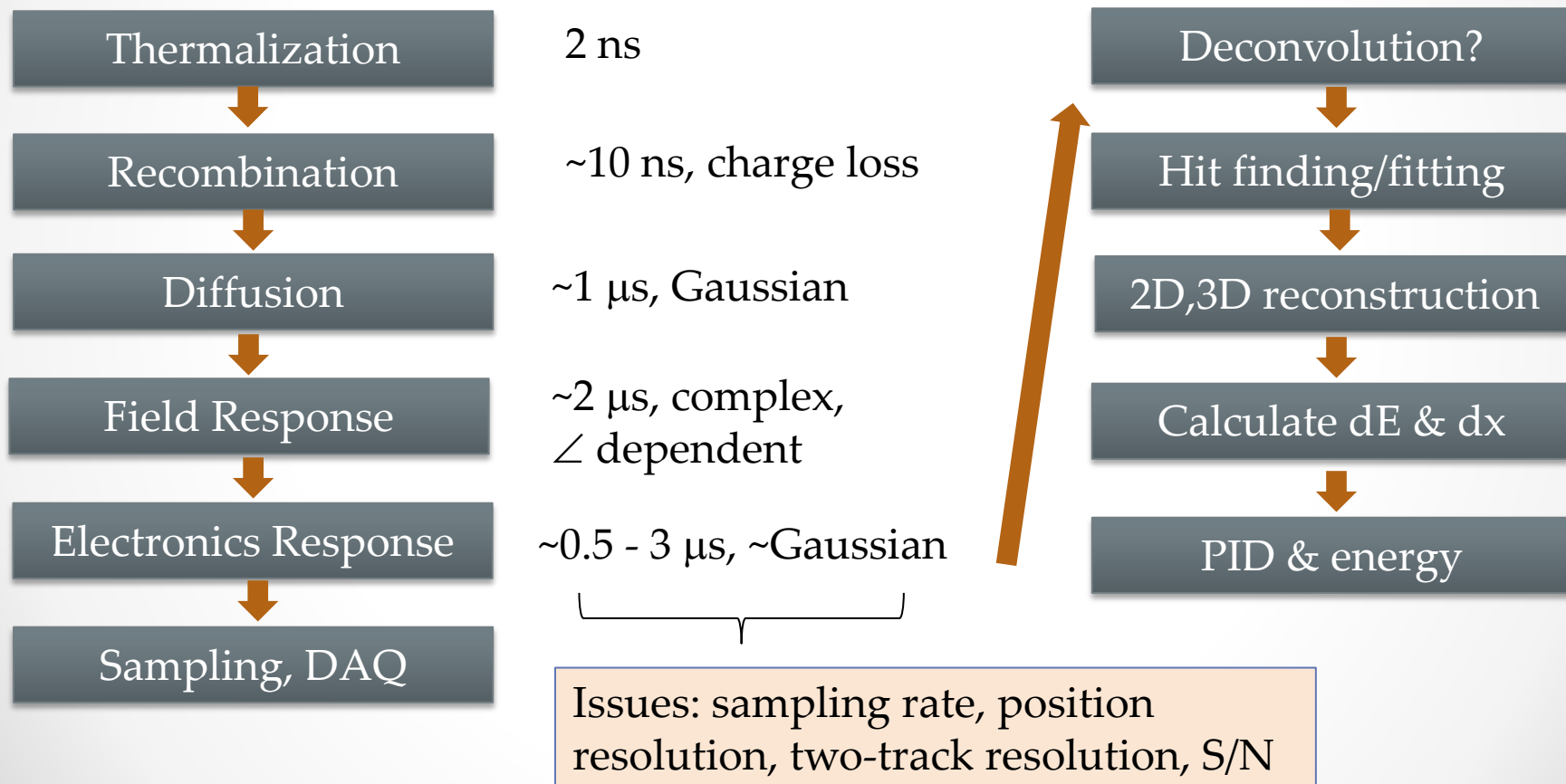
$$A_{300\text{K}} = 2 \times A_{90\text{K}}$$

$$B_{300\text{K}} = 2 \times B_{90\text{K}}$$

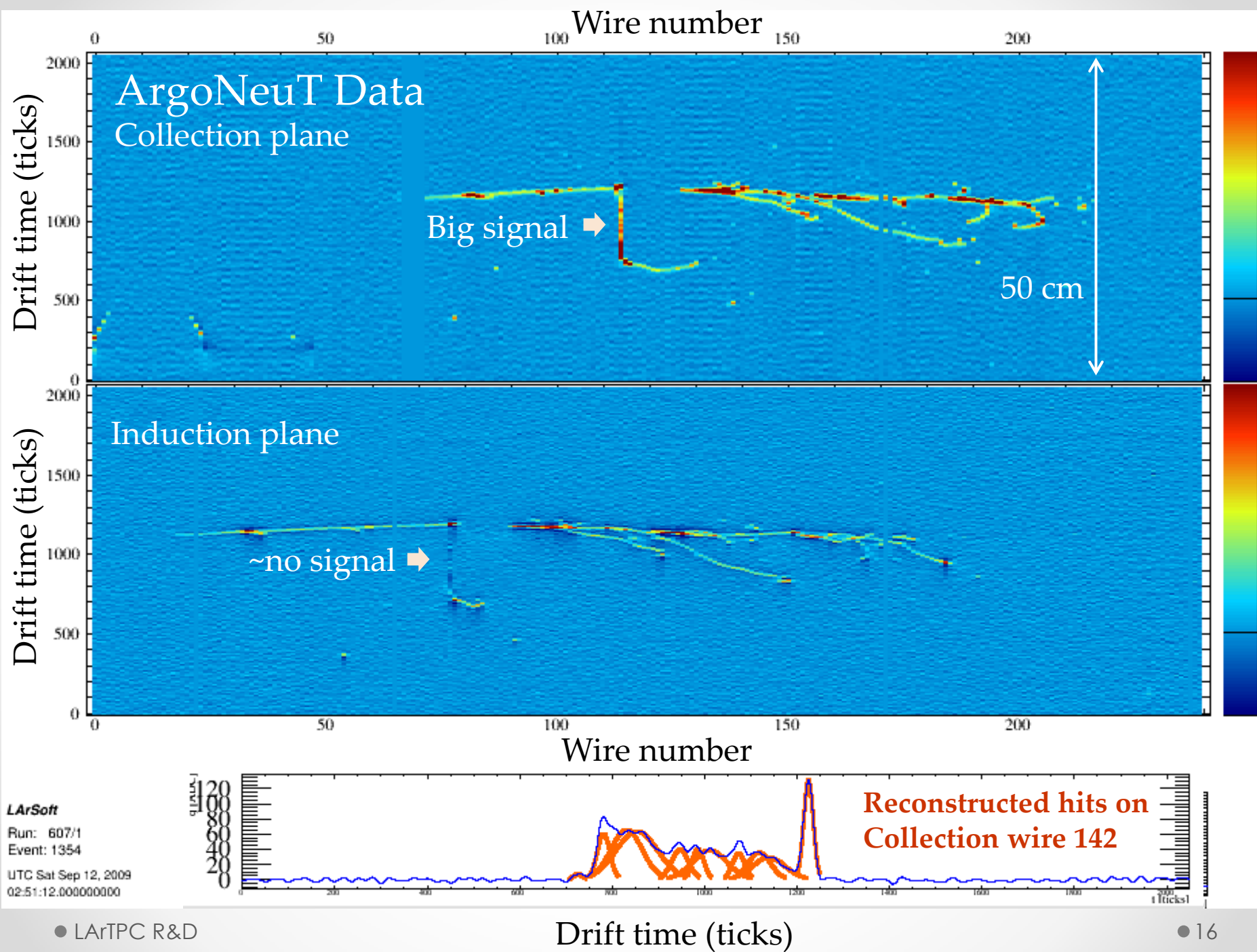


# Signal Processing Chain

Time spread, comments









# Convolution and Deconvolution

## Convolution

Signal = Ionization  $\otimes$  diffusion  $\otimes$  field  $\otimes$  electronics

$\mathcal{F}$  = Fourier Transform

$$\text{Signal} = \mathcal{F}^{-1} \{ (\mathcal{F}(\text{ionization}) * \mathcal{F}(\text{diffusion}) * \mathcal{F}(\text{field}) * \mathcal{F}(\text{electronics})) \}$$

Convolution kernel  $\mathcal{K}$

## De-convolution & Filter

$$\text{Ionization} \otimes \text{diffusion} = \mathcal{F}^{-1} \{ \text{Filter} * \mathcal{F}(\text{Signal}) / \mathcal{K} \}$$

Filter protects when  $\mathcal{K} \rightarrow 0$  or to remove coherent noise

# Generalization

Signal for single hit  
e.g. induction plane

Response  
Function

Desired Output  
Shape, e.g. Gaussian



Determine  $\mathcal{R}$

$$\mathcal{F}(\mathcal{R}) = \mathcal{F}(G_1) / \mathcal{F}(ADC_1)$$

De-convolute hits in  
the ADC channel to  
a Gaussian form

$$G_n = \mathcal{F}^{-1} \{ \text{Filter} * \mathcal{F}(ADC) / \mathcal{F}(\mathcal{R}) \}$$

Cons

Developing convolution kernels and filters takes special effort  
Computational cost

# Closing Comments

- In-liquid signal formation well understood
  - Charge loss due to recombination and electron attachment are not...
- Complex field response in the wire planes
  - Motivates setting electronics shaping time  $> \sim$  field response time spread
- BNL ASIC designed for LArTPCs
  - Programmable gain and shaping time
  - Peak amplitude independent of the shaping time
  - Charge injection calibration
- Deconvolute signals?
  - Bipolar induction plane signals  $\rightarrow$  unipolar collection plane signals
    - Common hit finding and hit reconstruction code
  - Convert to a “standard” shape, e.g. Gaussian
  - No obvious benefit for collection plane signals for long shaping times
  - Remove coherent noise using a notch filter
  - Computational and human cost of developing kernels & filters